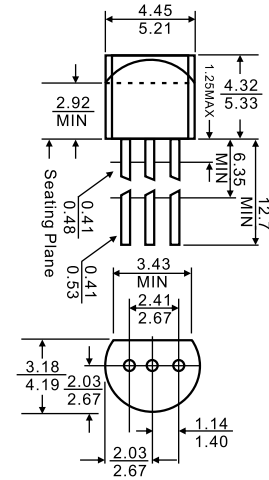


TO-92



1. EMITTER
2. COLLECTOR
3. BASE



Dimensions in inches and (millimeters)

Features

- ✦ Excellent h_{FE} linearity

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	500	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -6\text{V}$, $I_C = -20\text{mA}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240

Typical Characteristics

